SILICON (Si) POWER MOSFET A CEZC2351



CEZC2351

-150V ▲ 550mΩ ▲ -4.2A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type PN-channel enhancement mode UL94V-0 rated flame retardant epoxy PPAK3x3 package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability





RoHS

REACH

MAXIMUM RATINGS

Parameter ($T_A = 25^{\circ}C$, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	-150V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at R _{TH_JC}	I _D	-4.2A at T _c = 25°C
Continuous Drain Current at R _{TH_JA}	I _D	-1.3A at T _A = 25°C
Pulsed Drain Current at R _{TH_JC} Note 1	I _{DM}	-16.8A at T _c = 25°C
Pulsed Drain Current at R _{TH_JA} Note 1	I _{DM}	-5.2A at T _A = 25°C
Maximum Power Dissipation	PD	25W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case Note 2	R _{TH_JC}	5°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{th_ja}	50°C/W

APPLICATIONS

ССТV	Large	Pico	Power over	WIFI
	Displays	Cells	Ethernet	Hotspots
	\Box	5G/6G	РоЕ	WIFI

PIN DESCRIPTION

Circuit Diagram	Outline • Bottom View	Pin No.	Description
D (5) G (4) S (1,2,3)		1 2 3 4 5	Source Source Source Gate Drain

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ELECTRICAL CHARACTERISTICS A T_A = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250 \mu A$	BV _{DSS}	-150			V
Zero Gate Voltage Drain Current	$V_{DS} = -150V, V_{GS} = 0V$	I _{DSS}			-1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	V _{GS(th)}	-2		-4	V
Static Drain-Source On-Resistance	$V_{GS} = -10V, I_{D} = -2A$	R _{DS(ON)}		550	680	mΩ
Static Drain-Source On-Resistance	$V_{GS} = -6V, I_D = -1A$	R _{DS(ON)}		570	740	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = -50V, V_{GS} = 0V, f = 1MHz$	C _{ISS}		770		рF
Output Capacitance	V_{DS} = -50V, V_{GS} = 0V, f = 1MHz	Coss		55		рF
Reverse Transfer Capacitance	V_{DS} = -50V, V_{GS} = 0V, f = 1MHz	C _{RSS}		30		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = -75V, V_{GS} = 10V, I_{D} = -1A, $R_{\text{G}(\text{ext})}$ = 1 Ω	t _{D(ON)}		15		ns
Turn-On Rise Time	V_{DD} = -75V, V_{GS} = 10V, I_{D} = -1A, $R_{\text{G}(\text{ext})}$ = 1 Ω	t _R		5		ns
Turn-Off Delay Time	V_{DD} = -75V, V_{GS} = 10V, I_{D} = -1A, $R_{\text{G(ext)}}$ = 1 Ω	t _{D(OFF)}		33		ns
Turn-Off Fall Time	V_{DD} = -75V, V_{GS} = 10V, I_{D} = -1A, $R_{\text{G(ext)}}$ = 1 Ω	t _F		3		ns
Total Gate Charge	$V_{DS} = -75V, V_{GS} = -6V, I_D = -1A$	Q _G		11		nC
Gate Source Charge	$V_{DS} = -75V, V_{GS} = -6V, I_D = -1A$	Q _{GS}		2		nC
Gate Drain Charge	$V_{DS} = -75V, V_{GS} = -6V, I_D = -1A$	\mathbf{Q}_{GD}		5		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		١ _s			-4	А
Drain-Source Diode Forward Voltage Note 3	V _{GS} = 0V, I _S = -1.4A	V_{SD}			-1.2	V

Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board, t \leq 10 sec.

3: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

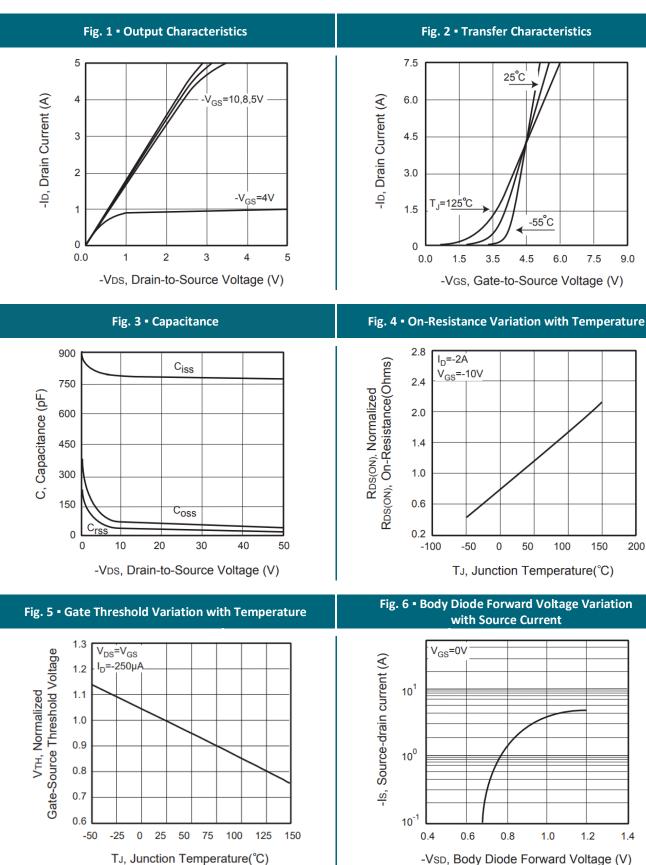
4: Guaranteed by design, not subject to production testing.



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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE



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REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

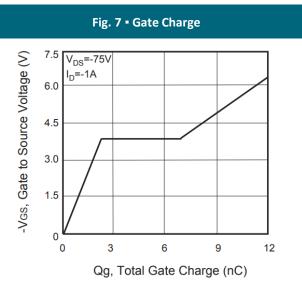
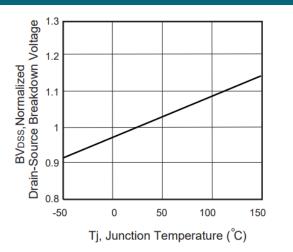
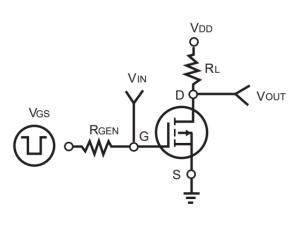


Fig. 9 - Breakdown Voltage Variation vs. Temperature







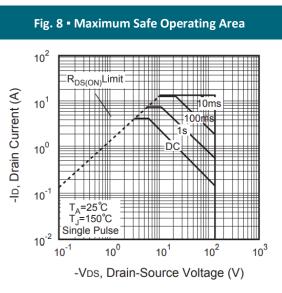
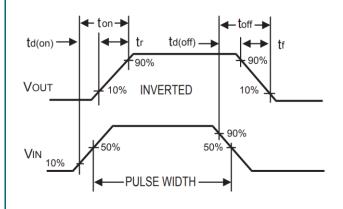


Fig. 11 - Switching Waveforms



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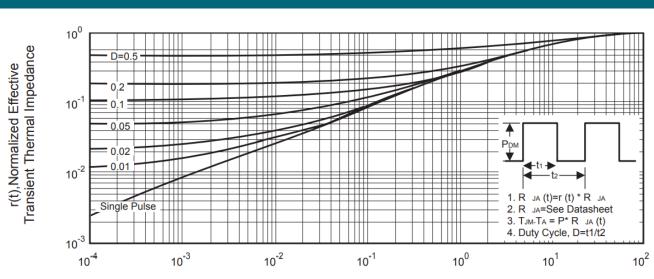
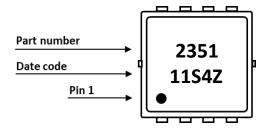


Fig. 12 • Normalized Thermal Transient Impedance Curve

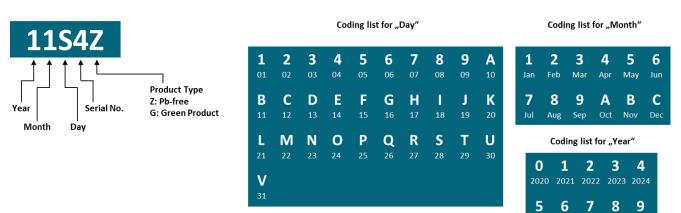
Square Wave Pulse Duration (sec)

PART MARKING



DATE CODE

Example: 11S4Z



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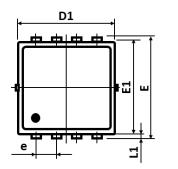
2025 2026 2027 2028 2029

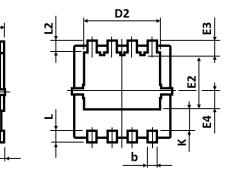
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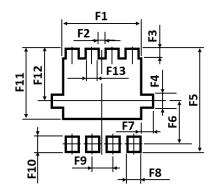


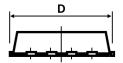
PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT

С









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	0.700	-	0.850	E2	1.540	-	1.940
b	0.200	-	0.400	E3	0.280	-	0.650
с	0.100	-	0.250	E4	0.370	-	0.770
D	3.000	-	3.450	е		0.650 (BSC)	
D1	3.000	-	3.250	К	0.500	-	0.890
D2	2.290	-	2.650	L	0.300	-	0.500
E	3.150	-	3.450	L1	0.060	-	0.200
E1	2.900	-	3.200	L2	0.270	-	0.570

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	2.500	-	F8	-	0.350	-
F2	-	0.300	-	F9	-	0.650	-
F3	-	0.400	-	F10	-	0.500	-
F4	-	0.430	-	F11	-	2.280	-
F5	-	3.350	-	F12	-	1.700	-
F6	-	1.400	-	F13	-	0.350	-
F7	-	0.420	-				

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEZC2351	PPAK 3x3	Reel	5,000pcs	10,000pcs	80,000pcs

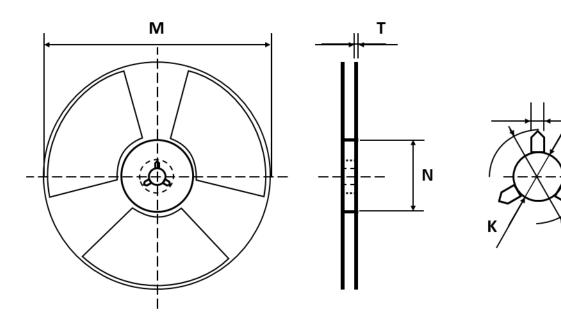


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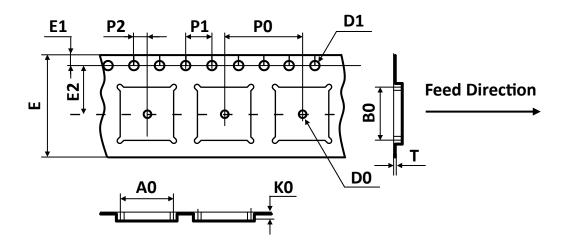


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	N	Т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
12mm	Ø330	±2.00	±1.00	±0.20	±0.50	+0.50 -0.20	±0.50

TAPE DIMENSIONS All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
	6.50	5.28	2.00	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
РРАК ЗхЗ	±0.10	±0.10	±0.10	±0.25	±0.10	+0.30 -0.10	±0.10	±0.05	±0.10	±0.10	±0.05	±0.02

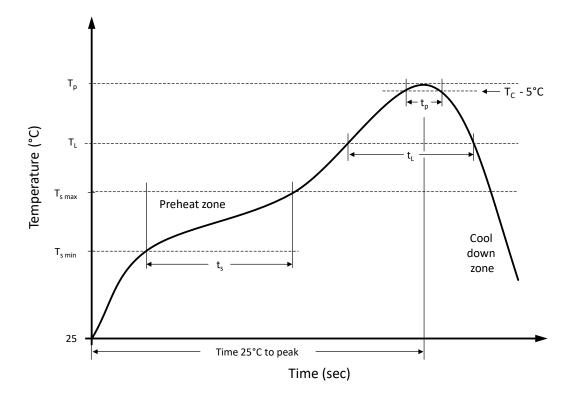


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RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time t_L maintained above T_L	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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